



Three-Phase Si-Bridge Rectifiers

DB 35-005 ... DB 35-16

Forward Current: 35 A

Reverse Voltage: 50 to 1600 V

Publish Data

Features

- Max. solder temperature: 260 °C, max. 5s
- UL recognized, file no. E63532
- $V_{ISO} > 2500 \text{ V}$

Mechanical Data

- Plastic case with alu-bottom
- Dimensions: 28,5 28,5 10 mm
- Weight approx. 23 g
- Standard packaging: bulk
- Terminals: plated terminals solderable per IEC 68-2-20
- Mounting position: any
- Admissible torque for mounting (M 5): 2 (± 10%) Nm

Type	Alternating input voltage V_{RMS} V	Repetitive peak reverse voltage V_{RRM} V
DB 35-005	35	50
DB 35-01	70	100
DB 35-02	140	200
DB 35-04	280	400
DB 35-06	420	600
DB 35-08	560	800
DB 35-10	700	1000
DB 35-12	800	1200
DB 35-14	900	1400
DB 35-16	1000	1600

Absolute Maximum Ratings $T_c = 25 \text{ °C}$ unless otherwise specified			
Symbol	Conditions	Values	Units
I_{FRM}	Repetitive peak forward current; $f > 15 \text{ Hz}^{1)}$	120	A
I^2t	Rating for fusing, $t < 10 \text{ ms}$	1000	A ² s
I_{FSM}	Peak forward surge current, 50 Hz half sine-wave $T_A = 25 \text{ °C}$	450	A
I_{FAV}	Max. averaged fwd. current, R-load, $T_A = 50 \text{ °C}^{1)}$	not applicable	A
I_{FAV}	Max. averaged fwd. current, C-load, $T_A = 50 \text{ °C}^{1)}$	not applicable	A
I_{FAV}	Max. current with cooling fin, R-load, $T_c = 100 \text{ °C}^{2)}$	35	A
I_{FAV}	Max. current with cooling fin, C-load, $T_c = 100 \text{ °C}^{2)}$	35	A
R_{thA}	Thermal resistance junction to ambient ¹⁾		K/W
R_{thC}	Thermal resistance junction to case ¹⁾	1,8	K/W
T_j	Operating junction temperature	- 50 ... + 150 °C	°C
T_s	Storage temperature	- 50 ... + 150 °C	°C

Characteristics $T_c = 25 \text{ °C}$ unless otherwise specified			
Symbol	Conditions	Values	Units
V_F	Maximum forward. voltage, $T_j = 25 \text{ °C}$; $I_F = 17,5 \text{ A}$	1,05	V
I_R	Maximum Leakage current, $T_j = 25 \text{ °C}$; $V_R = V_{RRM}$	10	μA
C_j	Typical junction capacitance per leg at V, MHz		pF



